

Substitute form 1449/APTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Sheet

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Of

1

Application Number

Complete if Known

10/706,641

Filing Date

11-12-2003

First Named Inventor

Allen

Group Art Unit

2826

Examiner Name

Unknown

Attorney Docket Number

5308-127DV

**U.S. PATENTS AND PATENT PUBLICATIONS**

Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code (if known)		
A7 ↓ ✓	1.	US-4,803,526		Terada et al.	02-07-1989
	2.	US-5,289,015		Chirovsky et al.	02-22-1994
	3.	US-5,300,795		Saunier et al.	04-05-1994
	4.	US-5,869,856		Kasahara, Kensuke	02-09-1999
	5.	US-2003/0017660 A1		Li, Weiqi	01-23-2003
	6.	US-5,891,769		Liaw et al.	04-06-1999

**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Cite No.	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T
		Office	Number	Kind Code (if known)			
A7 A2 A3	7.	JP	JP360189250 A		Onodera, Tsukasa	09-26-1985	Abstract Only
	8.	JP	JP404225534 A		Onodera, Tsukasa	08-14-1992	Abstract Only
	9.	JP	JP411150124 A		Yoshimura et al.	06-02-1999	Abstract Only

Examiner Signature

A7

Date Considered

9/30/05

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

**Complete if Known**

<b>Application Number</b>	<b>10/706,641</b>
<b>Filing Date</b>	<b>November 12, 2003</b>
<b>First Named Inventor</b>	<b>Scott T. Allen</b>
<b>Group Art Unit</b>	<b>2826</b>
<b>Examiner Name</b>	<b>Ahmed N. Sefer</b>
<b>Attorney Docket Number</b>	<b>5308-127DV</b>

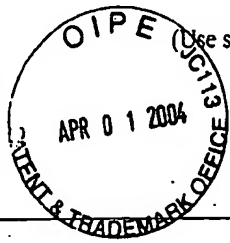
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<b>FORM PTO-1449 U.S. Department of Commerce</b> Patent and Trademark Office				Attorney Docket Number: 5308.127DV		Serial No.: 10/706,641	
<b>LIST OF DOCUMENTS CITED BY APPLICANT</b> <div style="display: flex; align-items: center; justify-content: center;">          (Use several sheets if necessary)       </div>							
Applicants: Allen et al.							
Filing Date: November 12, 2003						Group: 2826	
<b>U. S. PATENT DOCUMENTS</b>							
Examiner Initial...	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate	
AS	1	04/12/88	Stevens	437	33		
↓	2	04/26/94	O'Mara et al.	437	39		
↓	3	04/21/98	Tehrani et al.	257	280		
<b>FOREIGN PATENT DOCUMENTS</b>							
	Document Number	Date	Country	Class	Subclass	Translation Yes   No	
AS	4	WO 98/19342	05/07/98	PCT			
AS	5	WO 01/86727	11/15/01	PCT			
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							

Ex: AS

Date considered: 9/30/05

<b>FORM PTO-1449 U.S. Department of Commerce</b> <b>Patent and Trademark Office</b>  <b>LIST OF DOCUMENTS CITED BY APPLICANT</b>  (Use several sheets if necessary)					<b>Attorney Docket Number:</b> 5308-127DV		<b>Serial No.:</b> TBA	
					<b>Applicants:</b> Allen, et al.			
					<b>Filing Date:</b> Concurrently Herewith		<b>Group:</b>	
<b>U. S. PATENT DOCUMENTS</b>								
Examiner Initial	Serial Number	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate	
M	1.	US2003/0075719	04/2003	Sriram	257	77		
	2.	6,316,793	11/2001	Sheppard et al.	257	103		
	3.	6,218,680	04/2002	Carter, Jr. et al.	257	77		
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<b>FOREIGN PATENT DOCUMENTS</b>							
		Document Number	Date	Country	Class	Subclasses	Translation Yes   No
24.	24.	EP19900169	07/1999	European			
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V	58.	Noblanc et al., <i>Power Density Comparison Between Microwave Power MESFET's Processed on Conductive and Semi-Insulating Wafer</i> , Materials Science Forum, Vols. 338-342, 2000, pp. 1247-1250					

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